

Product data sheet

### 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4260QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

| Table 1. Quick reference data |                                         |                                                                                          |  |     |     |      |      |
|-------------------------------|-----------------------------------------|------------------------------------------------------------------------------------------|--|-----|-----|------|------|
| Symbol                        | Parameter                               | Conditions                                                                               |  | Min | Тур | Max  | Unit |
| V <sub>CEO</sub>              | collector-emitter<br>voltage            | open base                                                                                |  | -   | -   | -60  | V    |
| I <sub>C</sub>                | collector current                       |                                                                                          |  | -   | -   | -1.7 | А    |
| I <sub>CM</sub>               | peak collector current                  | $t_p \le 1 \text{ ms}; \text{ pulsed}$                                                   |  | -   | -   | -2.5 | А    |
| R <sub>CEsat</sub>            | collector-emitter saturation resistance | $I_C$ = -1 A; $I_B$ = -100 mA; pulsed;<br>$t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C |  | -   | 195 | 280  | mΩ   |

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#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

### 5. Pinning information

| Table 2. | Pinning | information |                                           |                |
|----------|---------|-------------|-------------------------------------------|----------------|
| Pin      | Symbol  | Description | Simplified outline                        | Graphic symbol |
| 1        | В       | base        |                                           | С              |
| 2        | Е       | emitter     |                                           | в-             |
| 3        | С       | collector   | 4 3                                       | ۲۹<br>۲۹       |
| 4        | С       | collector   |                                           | sym132         |
|          |         |             | Transparent top view DFN1010D-3 (SOT1215) |                |

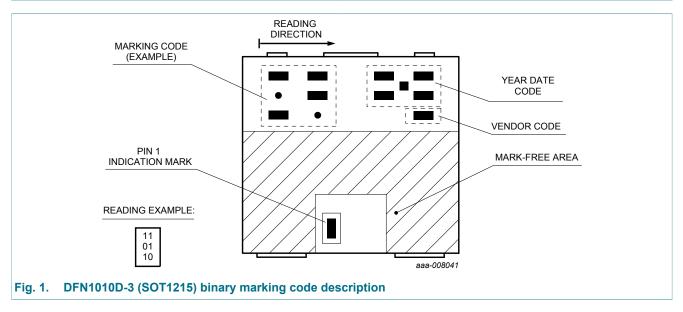
# 6. Ordering information

| Table 3. Ordering information |            |                                                                                  |         |  |  |
|-------------------------------|------------|----------------------------------------------------------------------------------|---------|--|--|
| Type number                   | Package    |                                                                                  |         |  |  |
|                               | Name       | Description                                                                      | Version |  |  |
| PBSS5260QA                    | DFN1010D-3 | plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals | SOT1215 |  |  |

### 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS5260QA  | 10 00 10     |



60 V, 1.7 A PNP low VCEsat (BISS) transistor

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                             |     | Min | Мах  | Unit |
|------------------|---------------------------|----------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                           |     | -   | -60  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                              |     | -   | -60  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                         |     | -   | -7   | V    |
| I <sub>C</sub>   | collector current         |                                        |     | -   | -1.7 | А    |
| I <sub>CM</sub>  | peak collector current    | $t_p \le 1 ms$ ; pulsed                |     | -   | -2.5 | А    |
| I <sub>B</sub>   | base current              |                                        |     | -   | -0.3 | А    |
| I <sub>BM</sub>  | peak base current         | $t_p \le 1 \text{ ms}; \text{ pulsed}$ |     | -   | -1   | А    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C               | [1] | -   | 325  | mW   |
|                  |                           |                                        | [2] | -   | 600  | mW   |
|                  |                           |                                        | [3] | -   | 740  | mW   |
|                  |                           |                                        | [4] | -   | 540  | mW   |
|                  |                           |                                        | [5] | -   | 1000 | mW   |
| Tj               | junction temperature      |                                        |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                        |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                        |     | -65 | 150  | °C   |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

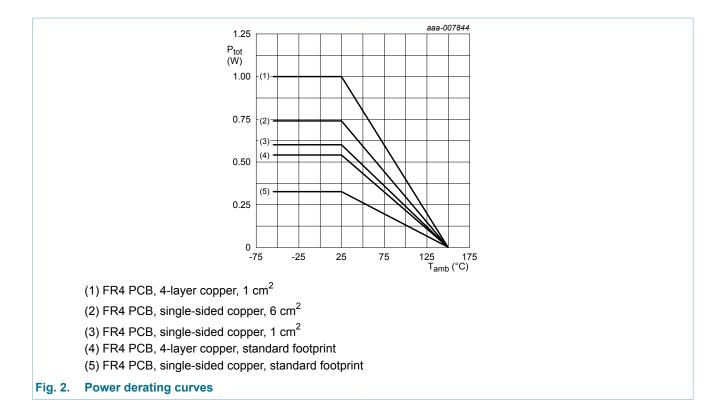
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

# PBSS5260QA

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



### 9. Thermal characteristics

| Table 6. T                  | able 6. Thermal characteristics |             |     |     |     |     |      |
|-----------------------------|---------------------------------|-------------|-----|-----|-----|-----|------|
| Symbol                      | Parameter                       | Conditions  |     | Min | Тур | Max | Unit |
| R <sub>th(j-a)</sub>        |                                 | in free air | [1] | -   | -   | 385 | K/W  |
| from junction to<br>ambient |                                 | [2]         | -   | -   | 209 | K/W |      |
|                             |                                 | [3]         | -   | -   | 169 | K/W |      |
|                             |                                 | [4]         | -   | -   | 232 | K/W |      |
|                             |                                 |             | [5] | -   | -   | 125 | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

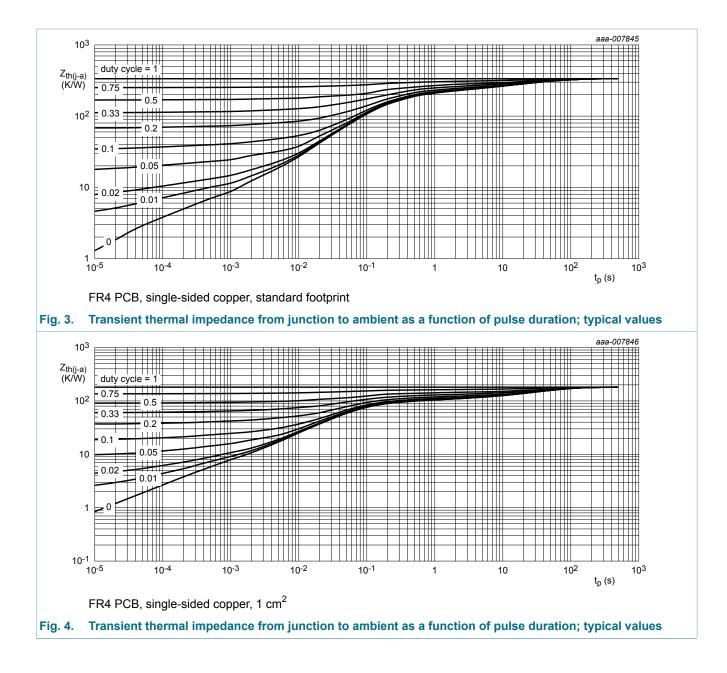
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

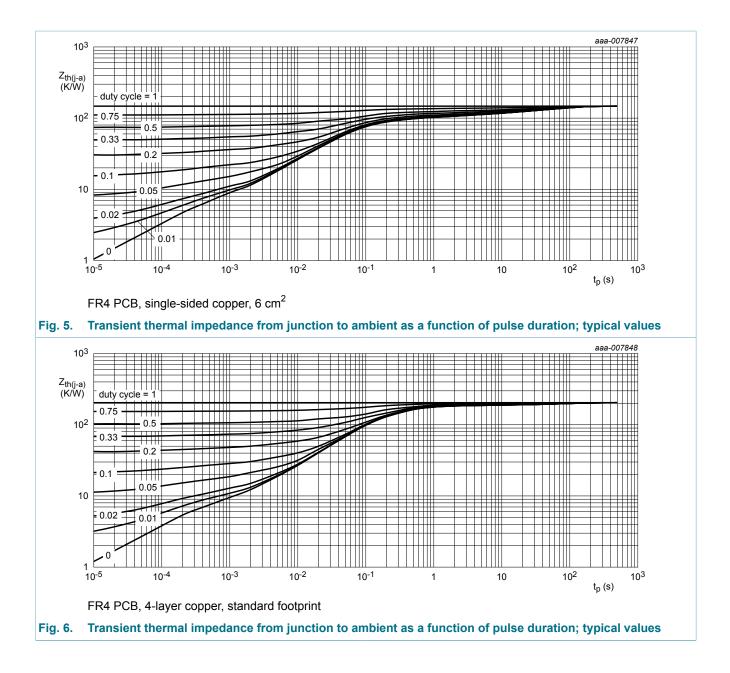


#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



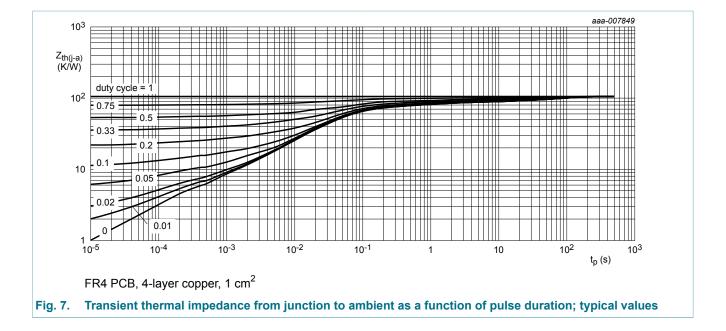


#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



# PBSS5260QA

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



### **10. Characteristics**

| Symbol                         | Parameter                            | Conditions                                                                                                                                                                                                      | Min | Тур  | Max  | Unit |
|--------------------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| I <sub>CBO</sub>               | collector-base cut-off               | V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                                                                                                                                         | -   | -    | -100 | nA   |
|                                | current                              | $V_{CB}$ = -48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                                                                                                                                                 | -   | -    | -50  | μA   |
| I <sub>CES</sub>               | collector-emitter cut-off current    | $V_{CE}$ = -48 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C                                                                                                                                                             | -   | -    | -100 | nA   |
| I <sub>EBO</sub>               | emitter-base cut-off current         | V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C                                                                                                                                          | -   | -    | -100 | nA   |
| h <sub>FE</sub> DC current gai | DC current gain                      | $V_{CE} = -2 \text{ V; } I_C = -100 \text{ mA; } t_p \le 300  \mu\text{s;}$<br>$\delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C; } \text{pulsed}$                                                             | 160 | 250  | -    |      |
|                                |                                      | $\label{eq:VCE} \begin{array}{l} V_{CE} = -2 \; V; \; I_{C} = -500 \; \text{mA}; \; t_{p} \leq 300 \; \mu \text{s}; \\ \delta \leq 0.02 \; ; \; T_{amb} = 25 \; ^{\circ}\text{C}; \; \text{pulsed} \end{array}$ | 120 | 185  | -    |      |
|                                |                                      | $\begin{split} V_{CE} &= -2 \text{ V}; \text{ I}_{C} = -1 \text{ A};  \text{t}_{p} \leq 300  \mu\text{s}; \\ \delta &\leq 0.02 ;  \text{T}_{amb} = 25 ^\circ\text{C}; \text{ pulsed} \end{split}$               | 85  | 125  | -    |      |
|                                |                                      | $V_{CE}$ = -2 V; I <sub>C</sub> = -1.7 A; pulsed;<br>t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C                                                                                        | 30  | 45   | -    |      |
| V <sub>CEsat</sub>             | collector-emitter saturation voltage | $I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; t_{p} \le 300 \mu\text{s};$<br>$\delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$                                                                     | -   | -105 | -155 | mV   |
|                                |                                      | $I_C$ = -1 A; $I_B$ = -50 mA; $t_p$ ≤ 300 μs;<br>δ ≤ 0.02 ; $T_{amb}$ = 25 °C                                                                                                                                   | -   | -280 | -400 | mV   |
|                                |                                      | I <sub>C</sub> = -1 A; I <sub>B</sub> = -100 mA; pulsed;<br>t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C                                                                                        | -   | -195 | -280 | mV   |

#### PBSS5260QA

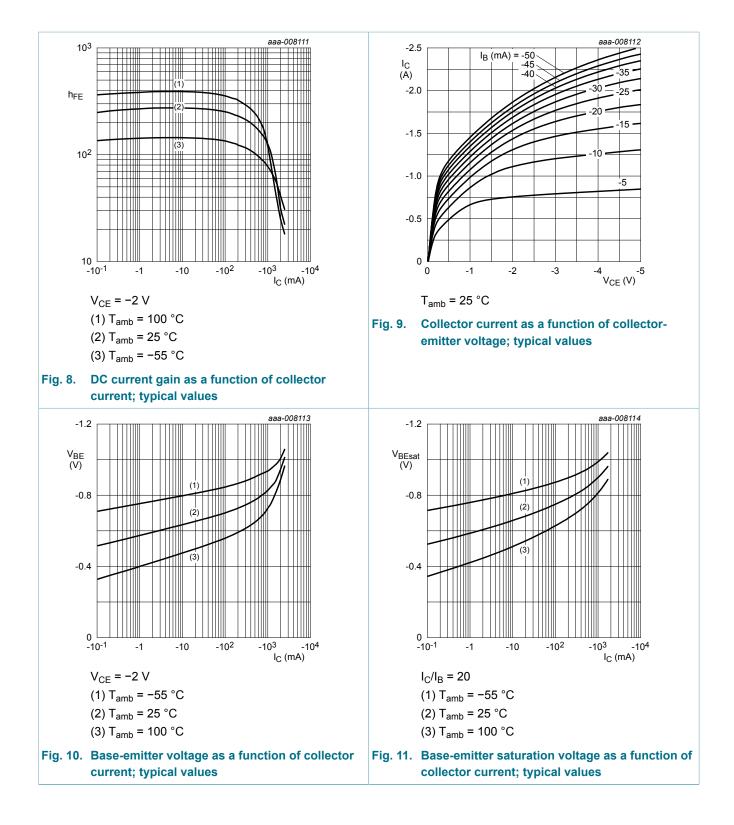
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# PBSS5260QA

### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

| Symbol             | Parameter                                                                                                 | Conditions                                                                                                                 | Min | Тур   | Мах   | Unit |
|--------------------|-----------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------|-----|-------|-------|------|
|                    |                                                                                                           | $I_{C}$ = -1.3 A; $I_{B}$ = -65 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C                   | -   | -480  | -700  | mV   |
|                    |                                                                                                           | $I_{C}$ = -1.7 A; $I_{B}$ = -170 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C                  | -   | -350  | -500  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance                                                                   | $I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; $T_{amb}$ = 25 °C                        | -   | 195   | 280   | mΩ   |
| V <sub>BEsat</sub> | base-emitter saturation voltage                                                                           | I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; pulsed;<br>t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C | -   | -0.85 | -1    | V    |
|                    |                                                                                                           | $I_C$ = -1 A; $I_B$ = -50 mA; pulsed;<br>$t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C                                      | -   | -0.88 | -1.05 | V    |
|                    |                                                                                                           | $I_{C}$ = -1.3 A; $I_{B}$ = -65 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C                   | -   | -0.91 | -1.1  | V    |
|                    | $I_{C}$ = -1.7 A; $I_{B}$ = -170 mA; pulsed;<br>$t_{p} \le 300 \ \mu$ s; δ $\le 0.02$ ; $T_{amb}$ = 25 °C | -                                                                                                                          | -1  | -1.15 | V     |      |
| V <sub>BEon</sub>  | base-emitter turn-on voltage                                                                              | $V_{CE}$ = -2 V; I <sub>C</sub> = -0.5 A; pulsed;<br>t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C   | -   | -0.78 | -0.9  | V    |
| t <sub>d</sub>     | delay time                                                                                                | $V_{CC}$ = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA;                                                      | -   | 15    | -     | ns   |
| t <sub>r</sub>     | rise time                                                                                                 | I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C                                                                        | -   | 35    | -     | ns   |
| t <sub>on</sub>    | turn-on time                                                                                              |                                                                                                                            | -   | 50    | -     | ns   |
| t <sub>s</sub>     | storage time                                                                                              |                                                                                                                            | -   | 300   | -     | ns   |
| t <sub>f</sub>     | fall time                                                                                                 |                                                                                                                            | -   | 50    | -     | ns   |
| t <sub>off</sub>   | turn-off time                                                                                             |                                                                                                                            | -   | 350   | -     | ns   |
| f <sub>T</sub>     | transition frequency                                                                                      | $V_{CE}$ = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C                                        | 100 | 150   | -     | MHz  |
| C <sub>c</sub>     | collector capacitance                                                                                     | V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C                | -   | 12    | 15    | pF   |

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

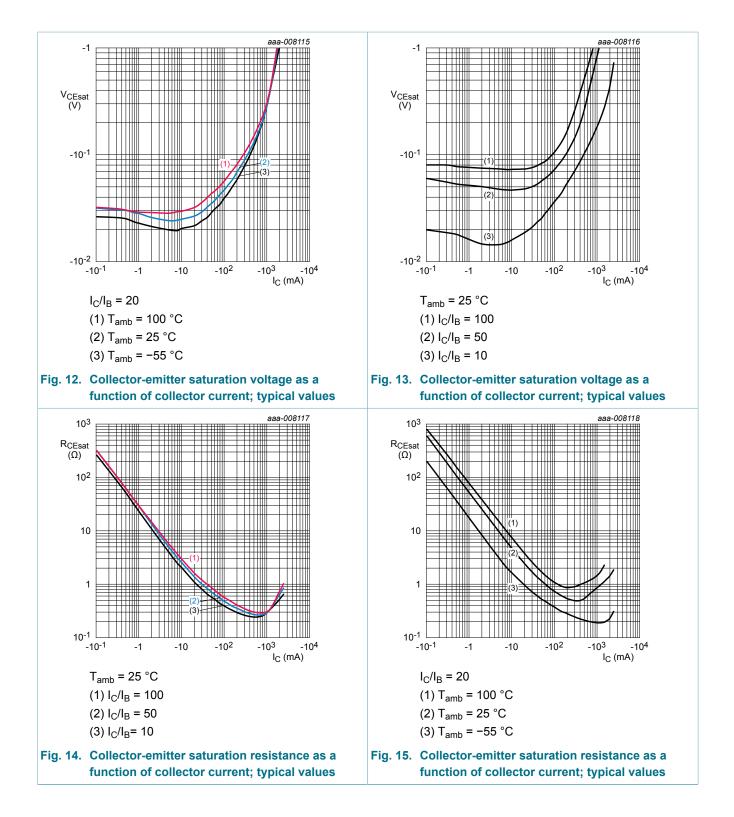


PBSS5260QA

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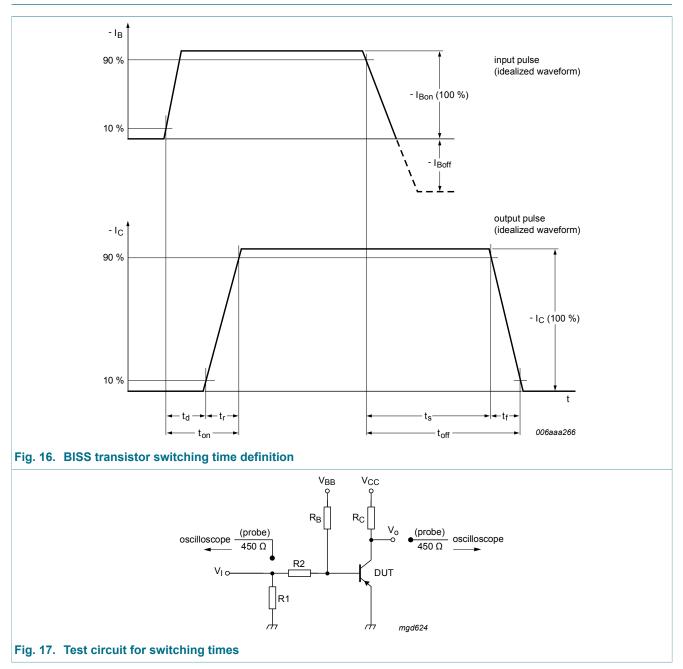
# PBSS5260QA

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



PBSS5260QA

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor



### 11. Test information

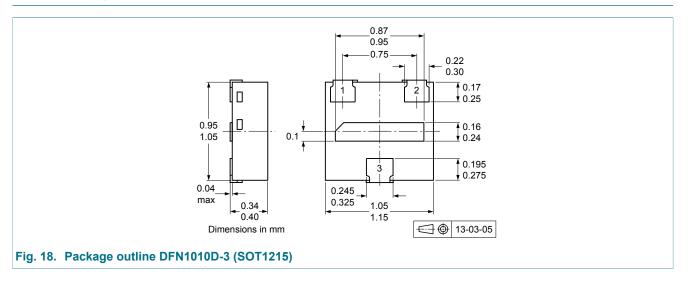


This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PBSS5260QA

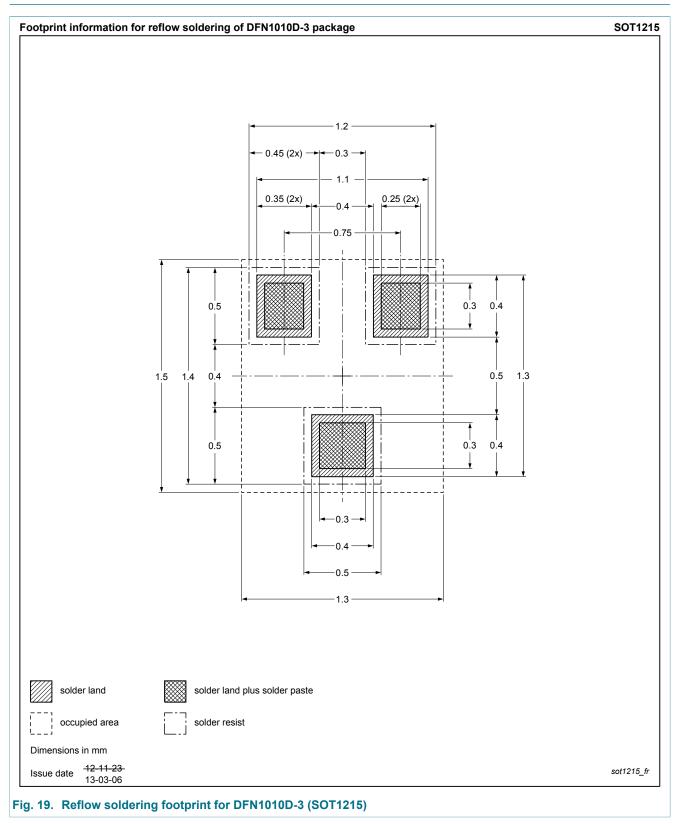
#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

# 12. Package outline



60 V, 1.7 A PNP low VCEsat (BISS) transistor

### 13. Soldering



### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

# 14. Revision history

| Fable 8.         Revision history |              |                    |               |            |  |
|-----------------------------------|--------------|--------------------|---------------|------------|--|
| Data sheet ID                     | Release date | Data sheet status  | Change notice | Supersedes |  |
| PBSS5260QA v.1                    | 20130828     | Product data sheet | -             | -          |  |

#### 60 V, 1.7 A PNP low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

| Document<br>status [1][2]            | Product<br>status [3] | Definition                                                                                  |
|--------------------------------------|-----------------------|---------------------------------------------------------------------------------------------|
| Objective<br>[short] data<br>sheet   | Development           | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production            | This document contains the product specification.                                           |

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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